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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Compleat if Kn wn <table border="1"> <tr> <td>Application Number</td> <td>09/905,536</td> </tr> <tr> <td>Filing Date</td> <td>July 13, 2001</td> </tr> <tr> <td>First Named Inventor</td> <td>Jerald P. Dykstra</td> </tr> <tr> <td>Group Art Unit</td> <td>2881</td> </tr> <tr> <td>Examiner Name</td> <td>N/A</td> </tr> <tr> <td>Attorney Docket Number</td> <td>11460-111</td> </tr> </table>		Application Number	09/905,536	Filing Date	July 13, 2001	First Named Inventor	Jerald P. Dykstra	Group Art Unit	2881	Examiner Name	N/A	Attorney Docket Number	11460-111
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Sheet	1	of	1														

Examiner Signature		Date Considered	03/21/2003
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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FORM PTO-1449
U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTORNEY DOCKET NO.: 11460-111

APPLICATION SERIAL NO.: 09/905,536

GROUP ART UNIT: 2881

APPLICANT: Jerald P. Dykstra

EXAMINER: N/A

FILING DATE: July 13, 2001

CONFIRMATION NO.: 3492

U.S. PATENT DOCKETS

EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS/SUB- CLASS	FILING DATE IF APPROPRIATE
LN	5,770,857	06/23/98	Fuerstenau et al.	250/281	11/15/96
LN	5,459,326	10/17/95	Yamada	250/398	01/09/95
LN	5,185,287	02/09/93	Aoyagi et al.	437/105	01/15/91
LN	5,166,521	11/24/92	Hayashi et al.	250/309	11/20/91
LN	5,111,042	05/05/92	Sullivan et al.	250/251	10/28/88
LN	4,737,637	04/12/88	Knauer	250/281	10/15/86

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS/SUB- CLASS	TRANSLATION YES NO
LN	JP 03245523A	11/01/91	Aoyanagi et al.		Abstract only
LN	JP 62112777 A1	11/11/85	Aoki		Abstract only
LN	DE 4135504A1	10/28/91	Falk et al.		Abstract only

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, etc.)

1.	N. Kofuji, et al., "Development of Gas Cluster Source and its Characteristics", Proc. 14th Symp. on Ion Sources and Ion-Assisted Technology, Tokyo (1991) @ pp. 15-18.
2.	Yamada, et al., "Cluster Ion Beam Processing", Matl. Science in Semiconductor Processing I, (1998) @ pp. 27-41.
3.	N. Toyoda et al., "Cluster Size Measurement of Large Ar Cluster Ions with Time of Flight", Proc. 1998 Intl. Conf. On Ion Implantation Technology, (1998) @ pp. 1234-1237.
4.	P. Milani, et al., "Plasma Cluster Beam Sources for Thin Film Deposition", AIP Conf. Proc. CP392, Part I, (1997) @ pp. 495-498.

EXAMINER

DATE CONSIDERED

03/21/2003